Recent research development of ferroelectric thin films

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Abstract: Recent research development of ferroelectric thin films has been introduced from the viewpoint of various electronic device application such as nonvolatile memory, infrared sensor, piezoelectric transducers and electrooptic devices. Explained materials of the ferroelectric thin films are PZT, Bi-layer-structured ferroelectrics, BiFeO3, YMnO3 and P (VDF-TrFE). © 2007 The Institute of Electrical Engineers of Japan.

Author Keywords: Ferroelectric thin films; Multiferroic; Nonvolatile memory; Sensor; Transducer

Year: 2007
Source title: IEEJ Transactions on Sensors and Micromachines
Volume: 127
Issue: 12
Page : 513-517
Link: Scorpus Link
Document Type: Review
Source: Scopus

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